$I_D(A)$

-4.8

-4.3



P-Channel 20-V (D-S) MOSFET-ESD Protected

FEATURES

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance
- ESD Protected

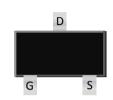
Application

- Portable Devices
- ■Consumer Electronics

SOT-23-3L

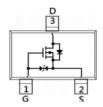
 V_{DS}

-20



27

38



PRODUCTY SUMMARY

@V_{GS}=-4.5V

@V_{GS}=-2.5V

 $R_{DS(on)} m(\Omega)$

Mechanical

●Case: SOT-23-3L Package

Packing Information

Package	Packing
SOT-23-3L	3Kpcs / 7" Reel

Maximum Ratings (T _A =25°C unless otherwise specified)							
Parameter	Symbol	Limit	Unit				
Drain-Source Voltage	V _{DS}	-20	V				
Gate-Source Voltage	V _{GS}	±8	V				
Continuous Drain Current 1)4)	I _D	-6.2	А				
Maximum Power Dissipation	P _D	0.5	W				
Pulsed Drain Current 2)	I _{DM}	-24.8	А				
Operating Junction and Storage Temperature Range	T _J , T _{STG}	-55 to 150	°C				

Typical Thermal Resistance						
Parameter	Symbol	Limit	Unit			
Junction-to-Ambient Thermal Resistance	$R_{\theta JA}$	100	°C/W			

Note:

R0JA is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper



Electrical Characteristics (T _A = 25°C UNLESS OTHERWISE NOTED)								
Characteristics	Symbol	Test Condition	Limits					
			Min	Тур	Max	Unit		
		Static						
Orain-Source Breakdown Voltage	B _{VDSS}	$V_{GS} = 0V, I_D = -250uA$	-20	-	-	V		
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=-250uA$	-0.5	-0.65	-0.84	V		
Drain-Source On-State Resistance	R _{DS} (on)	V _{GS} =-4.5V, I _D =-3.0A		23	27	mΩ		
	N _{DS} (OH)	V _{GS} =-2.5V, I _D =-3.0A		32	38	mΩ		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-20V, V _{GS} =0V		-	-1.0	uA		
Gate-Source Leakage Current	I _{GSS}	$V_{GS}=\pm 8V, V_{DS}=0V$		_	±100	nA		
		Dynamic ³⁾						
Total Gate Charge	Q_g		-	30	-	nC		
Gate-Source Charge	Q_{gs}	V_{DS} =-10V, I_{D} =-9.5A, V_{GS} =-5V	-	6	-	nC		
Gate-Drain Charge	Q_{gd}	, v _{GS} = ov	-	4	-	nC		
nput Capacitance	C _{iss}		-	2158	-	pF		
Output Capacitance	C _{oss}	V_{DS} =-15V, V_{GS} =0V, f=1.0MHZ	-	845	-	pF		
Reverse Transfer Capacitance	C _{rss}	1=1.0Wii 12	-	230	-	pF		
	1	1	l					
		Switching						
Turn-On Delay Time	t _{d(on)}	V_{DD} =-10V, I_{D} =-9.5A, V_{GS} =-4.5V,RG=6 Ω , R_{D} =1.05 Ω	-	25	-	ns		
Turn-On Rise Time	t _r		-	500	-	ns		
Turn-Off Delay Time	t _{d(off)}		-	70	-	ns		
Turn-Off Fall Time	t _f	_	-	300	-	ns		
	•	1	•					
	Dr	ain-Source Diode						
Maximum Continuous Body Diode Forward Current	Is	V _G =V _D =0V , Force Current	-	-	-1.2	А		
Diode Forward Voltage	V_{SD}	IS=-1.0A, VGS=0V	-	-	-1.5	V		

NOTES:

1. Pulse width<300us, Duty cycle<2%.

2. Essentially independent of operating temperature typical characteristics.

3. Repetitive rating, pulse width limited by junction temperature T_{,i}(MAX)=150°C. Ratings are based on low frequency and duty cycles to keep initial T_{,j}=25°C.

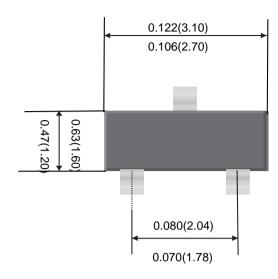
4. The maximum current rating is package limited.

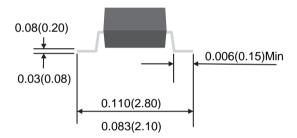
5. RQJA is the sum of the junctiontocase and casetoambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch2 with 2oz.square pad of copper.

6. Guaranteed by design, not subject to production testing.

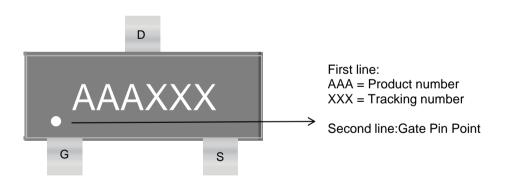


Package Outline Dimensions (inches and millimeters)





Marking Information



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